arXiv:2208.05188v2 [physics.app-ph] 12 Aug 2022

Tunneling transistor theoretical model based on changed operating principles

Pawel Pfeffer*
Institute of Physics, Polish Academy of Sciences,
Aleja Lotnikow 32/46, PL-02668 Warsaw, Poland

A tunneling transistor without heterojunction as a theoretical design is under consideration. The electrons from the conduction band of the source tunnel through the forbidden gap E_g of the channel to the conduction band of the drain. The tunneling current J calculations made for the Au-GaSe-Au and the InAs-InAs-InAs structures show that for a constant source-drain voltage, V_C, of several mV, changes in the gate voltage, V_G, applied to the channel within the voltage range of 0 - $E_g/2$e change J by even 10 orders of magnitude at helium temperature. Unlike the existing solutions such as tunnel field-effect-transistor (TFET), the proposed device uses the change of V_G, i.e. the change of the electrostatic potential in the channel, to modify the imaginary wave vector k_z of tunnel current electrons. Consequently, the gate voltage controls the damping force of the electrons wave functions and thus the magnitude of the tunneling current J.

I. INTRODUCTION

The tunnel current in the Metal-Insulator-Metal (M-I-M) structure has been theoretically described and experimentally tested for many years, starting in 1930 Ref.[1], see also e.g. Refs.[2]-[6]. The theoretical problem of the transmission of relativistic electrons through the potential barrier of a controlled height, described by the Dirac equation, called the Klein paradox, was published Ref.[7] and resolved many years ago, see review Ref.[8]. The similar theoretical problem, in close analogy to Dirac model, but for transmission coefficient of conduction electrons through the potential barrier with the height depending on the voltage applied to it, V_B, was solved for graphene Ref.[9], for phosphorus Ref.[10] and for IV-VI semiconductor compounds Ref.[11] in recent years. Both of these phenomena are the basis of the proposed theoretical tunneling transistor model. Thereby, the considered design, described below, differs from existing TFET solutions based on the fact that an increase in V_G means an increase of the bands bending in the source-channel heterojunction and, as a result, an increase in the tunnel current J from the valence band to the conduction band in $p^+ - i - n^+$ or $p^{++} - n^- - n^+$ configuration or from the conduction band to the valence band in $n^+ - i - p^+$ or $n^{++} - p^- p^+$ configuration (band-to-band tunneling (BTBT)) , see e.g. Refs.[12]-[16].

II. TUNNELING CURRENT IN METAL-INSULATOR-METAL STRUCTURE

Here we consider details of the general formula for the dependence of the current J on the applied voltage, V_C, in the M-I-M structure (see Ref. [3]) as the source-channel-drain structure in our design. The elements of this structure are selected so that current electrons from the metal A tunnel along the z direction through the forbidden gap of the insulator to the metal B, see Fig. 1. The wave vector $k_z(z)$ of the tunneling electrons has a decisive influence on the magnitude of the J current. This vector has an imaginary value and determines how much the electron wave function is damped in the insulator area.

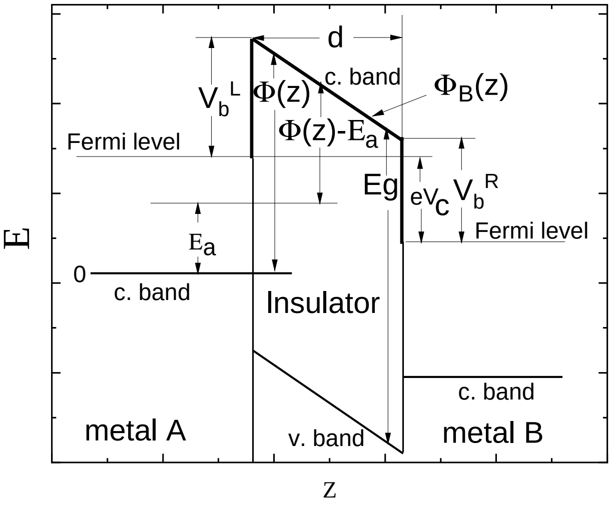

FIG. 1: Diagram of the Metal-Insulator-Metal structure with applied voltage V_C between the metal A and the metal B, see e. g. Ref.[3]. The tunneling current flows along the z direction from the metal A through the forbidden gap of the insulator to the metal B. V_b^L and V_b^R are the band offsets between the conduction band of the insulator and the Fermi energy E_F in the metal A or the metal B, respectively. E_a is the energy of the electron.

In order to determine formula for $|k_z(z)|$ we proceed as follows: the energy of electron in the insulator, $E(k)$, counted from the bottom of the forbidden gap, in the two band model, is:

$$E(k) = E_g - ((\Phi(z) - E_a) =$$

---

*pfeff@ifpan.edu.pl

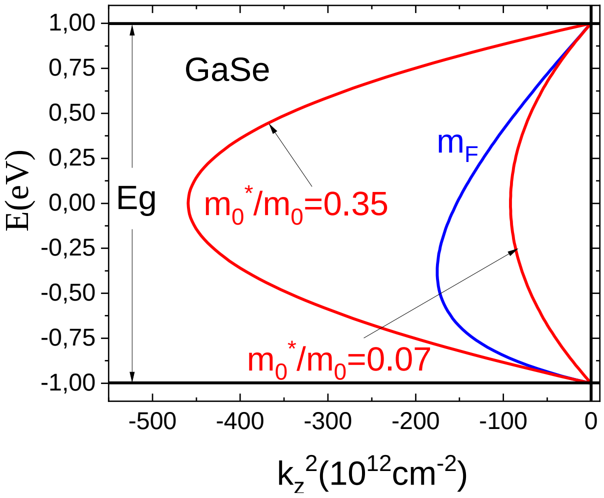

FIG. 2: The theoretical energy dispersions $E(k_z^2)$ in the forbidden gap of GaSe for $k_\perp = 0$. The blue curve includes the electron mass $m_F(E)$ calculated in the two level Franz model for $m_C/m_0 = 0.35$ and $m_V/m_0 = 0.07$. The red curves are calculated in the two level model for $m_0^*/m_0 = 0.35$ or $m_0^*/m_0 = 0.07$.

$$= \frac{E_g}{2} \pm \left[(\frac{E_g}{2})^2 + \frac{E_g \hbar^2 ({k_z^i}^2 + k_\perp^2)}{2m_0^*} \right]^{1/2} \quad , \qquad (1)$$

where E_g is the forbidden gap of the insulator, $k^2 = k_\perp^2 + k_z^i$, and wave vectors $k_\perp$ and k_z^i have real and imaginary value in E_g, respectively. E_a is the energy of the electron in the metal A, m_0^* is the effective electron mass m_c at the conduction-band edge or m_v at the valence-band edge corresponding to the sign in front of the square root in Eq.(1) and V_C is the applied voltage. $\Phi(z) = \Phi_B(z) + E_F$ is the energy of the M-I-M barrier potential relating to the metal A conduction band edge, where

$$\Phi_B(z) = V_b^L + (V_b^R - V_b^L - eV_c)z/d \quad , \qquad (2)$$

V_b^L and V_b^R are metal-insulator barrier energies and E_F is the Fermi energy.

Hence,

$$|k_z(z)| = \left[\left(1 - \frac{\Phi(z) - E_a}{E_g} \right) (\Phi(z) - E_a) \frac{2m_0^*}{\hbar^2} + k_\perp^2 \right]^{1/2} \quad . \qquad (3)$$

or

$$|k_z(z)| = \left[\left(1 - \frac{E(z)}{E_g} \right) E(z) \frac{2m_0^*}{\hbar^2} + k_\perp^2 \right]^{1/2} \quad . \qquad (4)$$

The next step is a general expression for the elastic tunneling current J(V) from the metal A to the metal B (e. g. Ref [5]),

$$J(V) = \frac{2eS}{\hbar} \int_0^\infty dE_a (f_A(E_a) - f_B(E_a)) \cdot$$

$$\cdot \int_0^\infty \frac{d^2 k_\perp}{(2\pi)^2} \exp \left[-2 \int_0^{\mathrm{d}} |\mathrm{k_z}|(\mathrm{k_\perp}, \Phi(\mathrm{z}) - \mathrm{E_a}) \mathrm{dz} \right] = \qquad (5)$$

$$= \frac{2eS}{\hbar} \int_0^\infty dE_a (f_A(E_a) - f_B(E_a)) \cdot$$

$$\cdot \int_0^\infty \frac{dk_\perp k_\perp}{2\pi} \exp \left[-2 \int_0^{\mathrm{d}} |\mathrm{k_z}|(\mathrm{k_\perp}, \Phi(\mathrm{z}) - \mathrm{E_a}) \mathrm{dz} \right] \quad ,$$

or

$$J(V)/S \left[\frac{A}{cm^2} \right] = \frac{7.7483}{10^5} \int_0^\infty dE_a (f_A(E_a) - f_B(E_a)) \cdot$$

$$\cdot \int_0^{k_\perp^M} dk_\perp k_\perp \exp \left[-2 \int_0^{\mathrm{d}} |\mathrm{k_z(z)}| \mathrm{dz} \right] \qquad (6)$$

where $k_\perp^M = k_\perp^F$ for E_F and k_z=0 in the M-I-M system. Further, d is the insulator thickness and S is the area of the interface between the metal and the insulator. $f_A(E_a)$ and $f_B(E_a)$ are F-D distribution functions for the metal A and the metal B, $f_A(E_a) = 1/[1 + \exp(\mathrm{E_a} - \mathrm{E_a^F})/\mathrm{kT}]$ and $f_B(E_a) = 1/[1 + \exp[\mathrm{E_a} - (\mathrm{E_a^F} - \mathrm{eV_C})]/\mathrm{kT}]$.

For very low temperature one has

$$J(V)[\frac{A}{cm^2}] = \frac{7.7483}{10^5} \cdot$$

$$\cdot \int_{E_F - eV}^{E_F} dE_a \int_0^{k_\perp^M} dk_\perp k_\perp \exp \left[-2 \int_0^{\mathrm{d}} |\mathrm{k_z(z)}| \mathrm{dz} \right] \quad , \qquad (7)$$

One can notice that the formula for $J(V)$ is dominated by the element with the exponential decay which is a result of the imaginary value of k_z in the electron wave function for the insulator forbidden gap. It is also seen that all electrons in the metal A with energy in the range $E_F - (E_F - eV_C)$ form the tunneling current from the metal A to the metal B. Furthermore, the tunneling current of the electron is the bigger the smaller $|k_z|$ it has.

III. DEPENDENCE OF CURRENT ELECTRONS ENERGY ON k_z^2 IN CHANNEL FORBIDDEN GAP

Henceforth, the term Metal-Insulator-Metal is replaced by the term Source-Channel-Drain, source and drain are metals or n type semiconductors and channel is a wide gap or narrow gap semiconductor.

The comparison of experimental data with theoretical calculations $J(V)$ in the structure under consideration shows that to describe the dispersion $E(k_z^2)$ of electronic states in the forbidden gap of a channel, for example GaSe or InAs, the two-band model is sufficient, see Refs.[5] and [4]. The knowledge of the dependence E on k_z^2 for $k_\perp = 0$ is the most important, because the greater the $k_\perp$, the greater the $|k_z|$ for keeping the electron energy unchanged. On the other hand, the tunnel

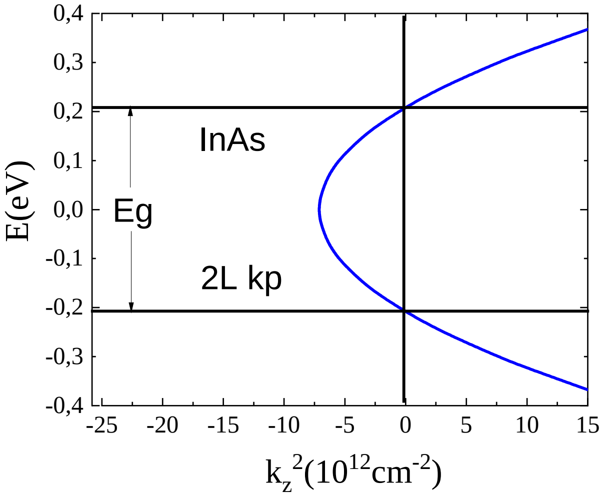

FIG. 3: The theoretical energy dispersion $E(k_z^2)$ in the forbidden gap of InAs for $k_\perp = 0$ calculated in the two level model for $E_g = 0.417$ eV and $m_0^*/m_0 = 0.026$.

current is determined by the electrons with $|k_z|$ as small as possible, i.e. with damping of their wave function as little as possible.

If the effective masses of electrons m_c and holes m_v are not equal the use of the two band Franz model for band-to-band tunneling, see Refs [17] and [18], allows for a more detailed description of the tunneling process. It means replacing m_0^* in Eq.(1) by m_F, the value of which depends on the energy of the electron E in the band forbidden gap. m_F has the form

$$m_F(E) = \frac{m_c}{(E/E_g)(1 - m_c/m_v) + m_c/m_v} \quad , \tag{8}$$

where $E = E_g - \Phi(z) + E_a$, see Fig. 1. It is seen that for $E = 0$ $m_F = m_v$ and for $E = E_g$ $m_F = m_c$.

To calculate the energy dispersion $E(k_z^2)$ in the forbidden gap of GaSe for $k_\perp = 0$ we used Eq. (3) with $m_0^* = m_F$ and GaSe parameters (Ref.[5]) $E_g = 2$ eV $m_C/m_0 = 0.35$ and $m_V/m_0 = 0.07$. The curves calculated for $m_0^* = m_F$, $m_0^* = m_C$ and $m_0^* = m_V$ are shown in Fig. 2. From comparison of the curves it follows that the use of $m_F(E)$ is necessary. The results of similar calculations for InAs are shown in Fig. 3. InAs parameters are $E_g = 0.417$ eV and $m_0^*/m_0 = 0.026$. Fig. 2 and Fig. 3 show that a slight change in the energy of the electron in the band gap significantly changes the value of k_z^2 of the electron, i.e. its importance in the formation of the tunnel current.

IV. PRINCIPLES OF OPERATION OF THE PROPOSED TUNNELING TRANSISTOR

The basis of the proposed transistor is the observation that the current that flows through the Source-Channel-Drain structure biased with the constant voltage V_C can be changed depending on the magnitude of the gate voltage V_G applied to the channel by electrode separated from the channel by the oxide layer. In other words, by increasing or lowering the potential energy of the channel in relation to the source, we can control k_z^2 of the current electrons, and thus the magnitude of the tunneling current, see Figs. 2 and 3. So, the modified formula for the $|k_z(z)|^2$ of an electron in the forbidden channel gap with the applied voltage V_G looks like this

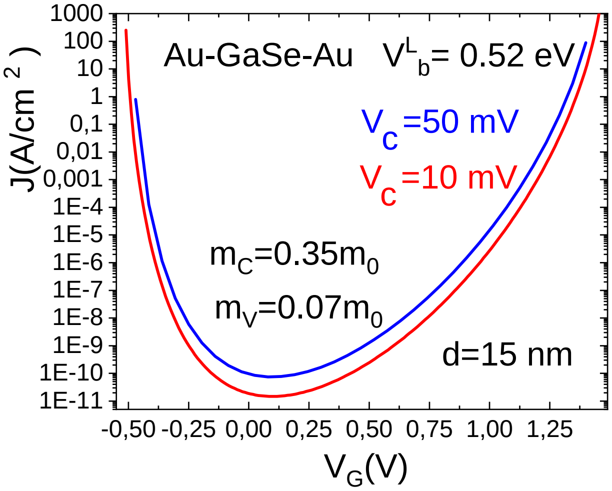

FIG. 4: The theoretical tunneling current J versus gate voltage V_G applied to the GaSe barrier. The curves calculated for different valus of voltage V_C applied to Au-GaSe-Au structure. For V_G in the range $(V_C - V_b^L)$ - $(E_g/e - V_C - V_b^L)$, the electrons tunnel through the whole width of the GaSe forbidden gap, see Fig 1. Changing the value of V_G shifts GaSe on the energy axis, thereby changes the value of energy, $E(k_z)$, and the value of the wave vector, k_z, of electrons in the forbidden gap, (see Fig. 2) and, as a result, leading to the exponential change in the value of the tunneling current, see Eq. (6). The width of GaSe part d = 15 nm and V_b^L=V_b^R=0.52 eV.

$$|k_z(z)|^2 = \left(1 - \frac{E(z) - eV_G}{E_g}\right)(E(z) - eV_G)\frac{2m_0^*}{\hbar^2} + k_\perp^2 \; . \tag{9}$$

In Fig. 4 is shown the dependence of the tunneling current J on the voltage V_G applied to the GaSe element with a width of $d = 15$ nm in the Au-GaSe-Au structure with $V_C = 10$ mV or 50 mV. A negative or positive value of V_G means reduction or increase of the virtual shift of V_b^L and V_b^R of the GaSe barrier with respect to the Au source, and thus the change k_z^2 of current electrons. The dependence $J(V_G)$ is seen also in Figs. 5 and 6 for the InAs-InAs-InAs structure with a width of $d = 50$ nm or 65 nm respectively, for different values of V_C. The electrons tunnel through the forbidden gap along the entire length of the channel for the value of V_G within the range V_C - $(E_g/e - V_C)$, see Fig. 7. The theoretical curves in the above cases are calculated using Eqs. 7 and 9. The

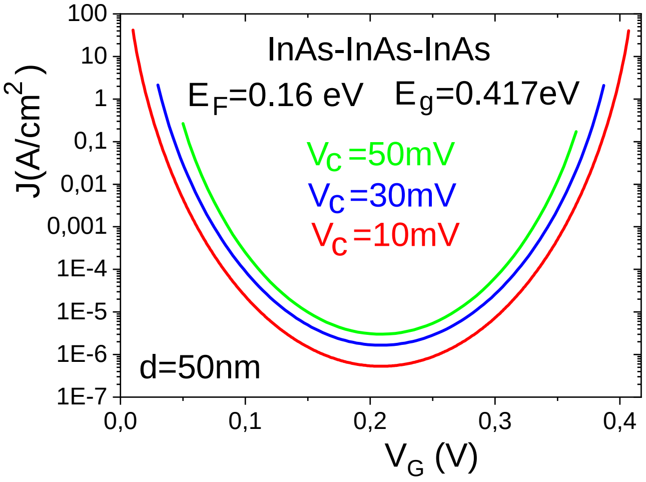

FIG. 5: The theoretical tunneling current J versus gate voltage V_G applied to the InAs barrier. The curves are calculated for different valus of voltage V_C applied to the InAs-InAs-InAs structure. The width of the barrier $d = 50$ nm and electron effective mass $m_0^*/m_0 = 0.026$. It is seen that a slight change of V_G can change the value of the tunneling current J by a few orders of magnitude.

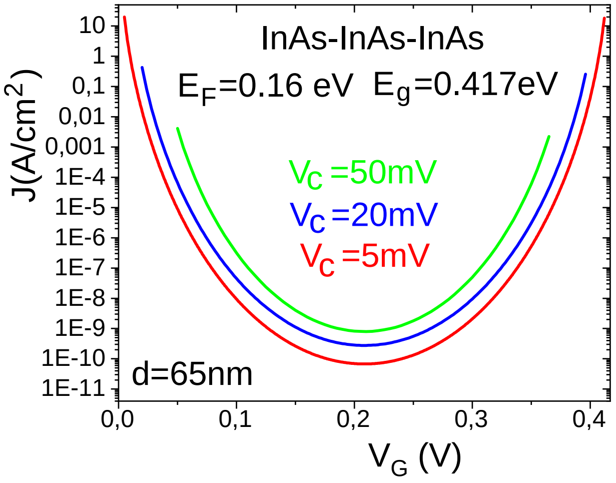

FIG. 6: The theoretical tunneling current J versus the gate voltage V_G applied to the InAs barrier of width $d = 65$ nm in the InAs-InAs-InAs structure. A comparison of Figs. 5 and 6 shows the strong dependence of tunneling current on the barrier width.

comparison of Figures 5 and 6 shows a clear dependence of the current J on the size of the electrons tunneling path d.

The conclusion that can be drawn from the $J(V_G)$ curves in Figures 4, 5 and 6 is as follows: the smaller V_C, the greater the ratio of the maximum tunnel current J_{MAX} to the minimum tunnel current J_{MIN}. The reason is that the smaller V_C and, consequently, J_C, the fewer electrons forming the current and the smaller the difference between $|k_z|^2$ of these electrons. Thus, the highest ratio of J_{MAX} to J_{MIN} for a given width of d will occur when the voltage V_C will be extremely small, i.e. when the tunneling current will be formed exclusively from electrons of the same energy E. In this case, it is convenient to calculate the transmission coefficient TC of electrons tunneling through the forbidden gap of the channel vs. V_G, (the procedure is included e.g. in Ref.[11]). Such a dependence $TC(V_G)$ for the InAs-InAs-InAs structure is shown in Fig. 8. It can be seen that the ratio of TC_{MAX} to TC_{MIN} and therefore J_{MAX} to J_{MIN} is indeed extremely large.

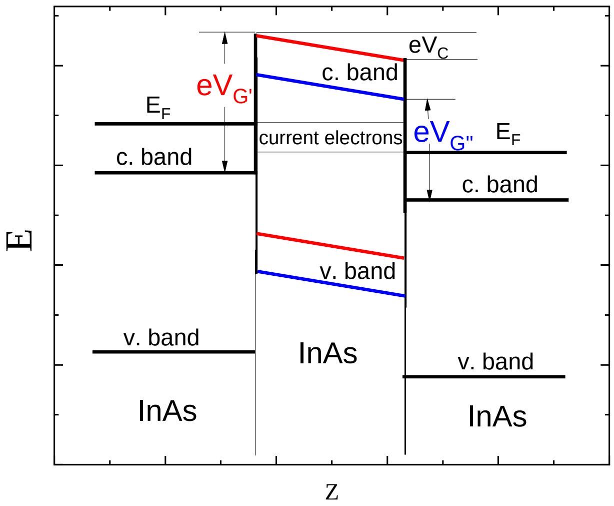

FIG. 7: Diagram of the proposed InAs-InAs-InAs tunneling transistor for the source-drain voltage V_C and for two different values of the gate voltage $V_{G'}$ and $V_{G''}$ applied to the channel. It is seen that the current electrons with energy in the range E_F - (E_F - eV_C) tunnel through a barrier with a V_G-dependent height, i.e. through energetically different parts of the forbidden gap of the channel.

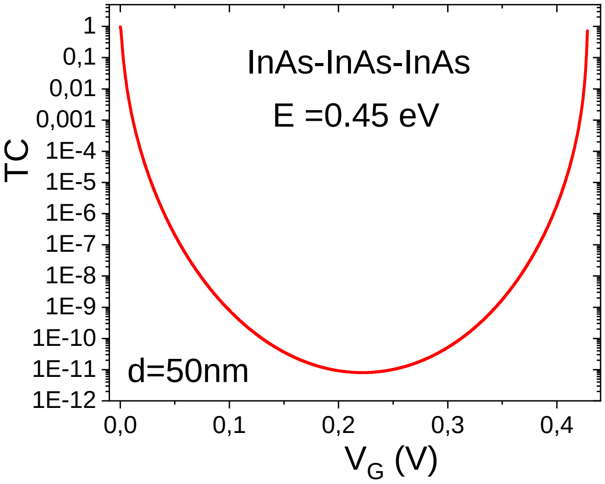

FIG. 8: Transmission probability T_C for electrons with specific value of E within forbidden gap of InAs versus barrier potential V_G. The curve calculated for values of V_G in the range 0 - E_g/e.

V. SUMMARY

The presented theoretical design of a tunneling transistor is a simple extension of the structure for studying the dependence of tunnel current on applied voltage. It has no heterojunction like TFET and is based on controlling the height of the potential barrier created by the channel biased with voltage V_G. Such a transistor would be extremely convenient in terms of technology. It is enough to apply a constant source-drain voltage V_C of a few mV and then small change of the gate voltage V_G applied to the channel changes the J value by a few orders of magnitude. The maximum computed change in J formed by tunneling electrons along the entire length of the channel is due to a change in V_G in the range 0 - $(E_g/2e - V_C)$. For an InAs structure with $d = 65$ nm, this means a change in V_G from 0 to about 200 mV and, consequently, a change in J by 9 orders of magnitude at $V_C = 20$ meV and by more than 6 orders of magnitude at $V_C = 50$ meV. The intensity of the tunneling current J can be additionally adjusted by changing the voltage V_C and the width d of the channel.

References

[1] J. Frenkel, Phys. Rev. **36**, 1604 (1930).
[2] J. G. Simmons, J. Appl. Phys. **34**, 1793 (1963).
[3] R. Stratton, G. Lewicki and C. A. Mead, J. Phys. Chem. Solids. **27**, 1599 (1966).
[4] G. H. Parker and C. A. Mead, Phys. Rev. Lett. **21**, 605 (1968).
[5] S. L. Kurtin, T. C. McGill, and C. A. Mead, Phys. Rev. B **3**, 3368 (1971).
[6] P. Zhang, Scientific Reports **5**, 9826 (2015).
[7] O. Klein, Z. Phys. **53**, 157 (1929).
[8] A. Calogeracos and N. Dombey, Contemp. Phys. **40**, 313 (1999).
[9] M. I. Katsnelson, K. S. Novoselov and A. K. Geim, Nat. Phys. **2**, 620 (2006).
[10] Zhenglu Li, Ting Cao, Meng Wu, and Steven G. Louie, Nano Letters **17**, 2280 (2017).
[11] P. Pfeffer, W. Zawadzki and K. Dybko, Semicond. Sci. Technol. **36**, 045023 (2021).
[12] D. Sarkar et al, Nature **526**, 91 (2015).
[13] U. E. Avci, D. H. Morris, and I. A. Young, J. Electron Devices Soc. **3**, 88 (2015).
[14] D. Verreck, A. S. Verhulst, and G. Groeseneken, *The Tunnel Field-Effect Transistor*, Wiley Encyclopedia of Electrical and Electronics Engineering, 1-24, (2016), library.wiley.com/doi/10.1002/047134608X.W8333.
[15] H. Ilatikhameneh, G. Klimeck, J. Appenzeller, and R. Rahman, arXiv:1603.09402v1 [cond-mat.mes-hall] 2016.
[16] C. Convertino et al, J. Phys. Condens. Matter **30**, 264005 (2018).
[17] W. Franz, (in German), Ann. Phys. **6**, 17 (1952).
[18] Y. Taur and J. Wu, IEEE Transactions on Electron Devices, **63**, 869 (2016).